GSM0906

100V N-Channel MOSFETs

Product Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are well suited for high efficiency fast switching applications.

Features

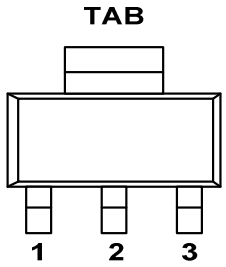
- 100V, 6.5A, $R_{DS(ON)}$=95mΩ@V_{GS}=10V
- Improved dv/dt capability
- Fast switching
- 100% EAS guaranteed
- Green Device Available
- SOT-223 package design

Applications

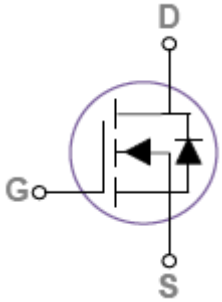
- Notebook
- Load Switch
- LED applications

Packages & Pin Assignments

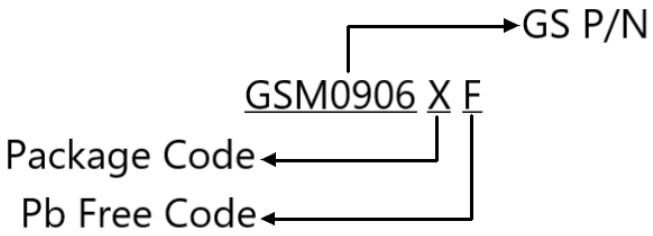
GSM0906XF (SOT-223)



Pin	Description
1	Gate
2	Drain
3	Source

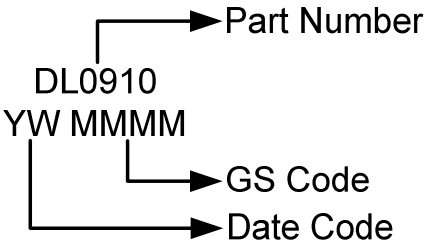


Ordering Information



Part Number	Package	Quantity
GSM0906XF	SOT-223	2500pcs

Marking Information



Absolute Maximum Ratings

T_C=25ºC Unless otherwise noted

Symbol	Parameter		Typical	Unit
V_{DS}	Drain-Source Voltage		100	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C=25℃	6.5	A
		T_C=100℃	4.1	
I_{DM}	Pulsed Drain Current[1]		26	A
P_D	Power Dissipation (T_A=25℃)		9	W
	Power Dissipation (Derate above 25℃)		0.072	W/℃
T_J	Operating Junction Temperature Range		-50 to +150	℃
T_{STG}	Storage Temperature Range		-50 to +150	℃
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		62	℃/W
$R_{\theta JC}$	Thermal Resistance-Junction to Case		14	℃/W

Electrical Characteristics

T_J=25℃ Unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250uA	100			V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃, I_D=1mA		0.05		V/℃
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250uA	1.2	1.6	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient			-5		mV/℃
I_{GSS}	Gate-Source Leakage Current	V_{DS}=0V,V_{GS}=±20V			±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=100V,V_{GS}=0V			1	uA
		V_{DS}=80V,V_{GS}=0V, T_J=125℃			10	
I_S	Continuous Source Current	V_G=V_D=0V, Force Current			6.5	A
I_{SM}	Pulsed Source Current				26	
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=10V,I_D=5A		80	95	mΩ
		V_{GS}=4.5V,I_D=3A		85	110	
g_{FS}	Forward Transconductance	V_{DS}=10V,I_D=3A		8.7		S
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=1A			1	V
Dynamic						
Q_g	Total Gate Charge[2,3]	V_{DS}=48V,V_{GS}=10V, I_D=5A		22	44	nC
Q_{gs}	Gate-Source Charge[2,3]			3.9	8	
Q_{gd}	Gate-Drain Charge[2,3]			5.2	10	
C_{iss}	Input Capacitance	V_{DS}=50V,V_{GS}=0V, f=1MHz		1480	2150	pF
C_{oss}	Output Capacitance			480	700	
C_{rss}	Reverse Transfer Capacitance			35	55	
$t_{d(on)}$	Turn-On Time[2,3]	V_{DD}=30V,I_D=1A, V_{GS}=10V,R_G=3.3Ω		2.9	6	ns
t_r				9.5	18	
$t_{d(off)}$	Turn-Off Time[2,3]			18.4	35	
t_f				5.3	10	
R_g	Gate Resistance	V_{DS}=0V,V_{GS}=0V, f=1MHz		1.3	2.6	Ω

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

Typical Performance Characteristics

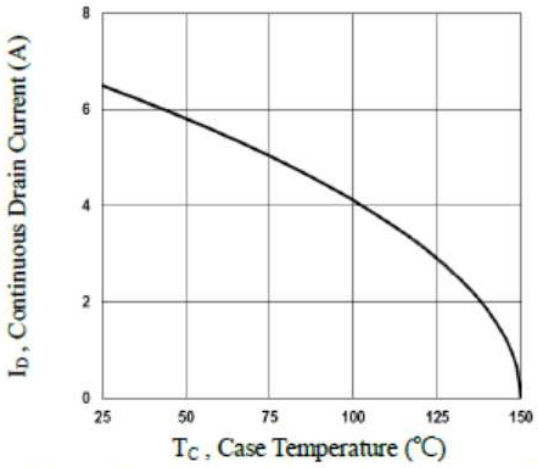


Fig.1 Continuous Drain Current vs. T_C

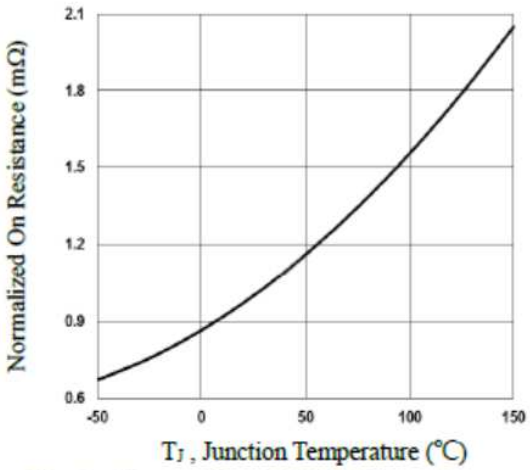


Fig.2 Normalized RDSON vs. T_J

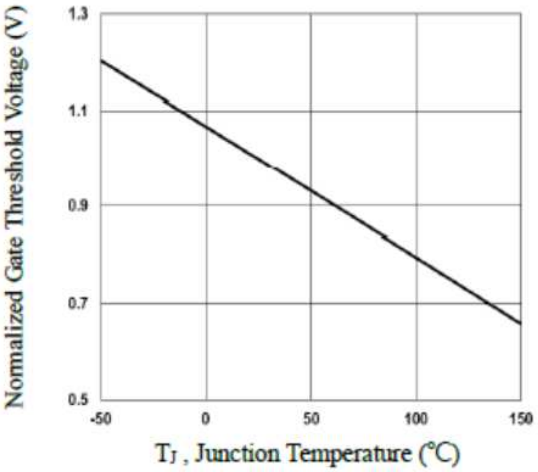


Fig.3 Normalized V_{th} vs. T_J

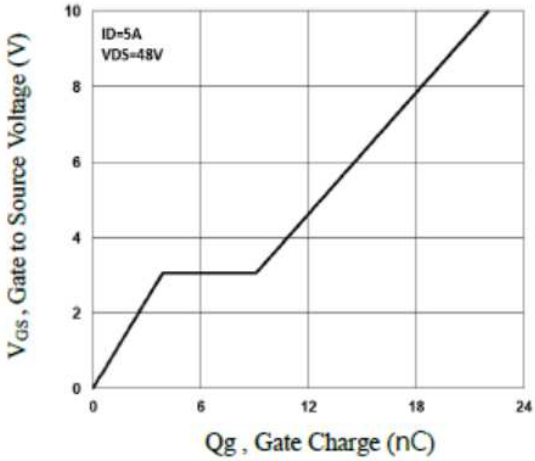


Fig.4 Gate Charge Waveform

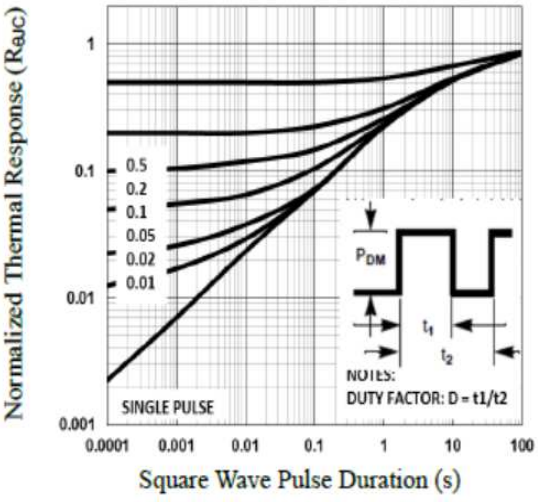


Fig.5 Normalized Transient Impedance

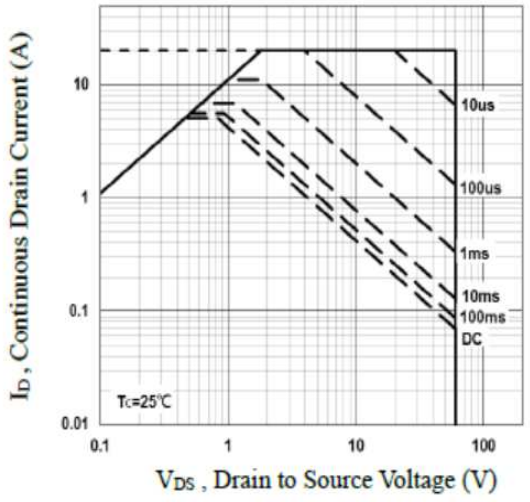
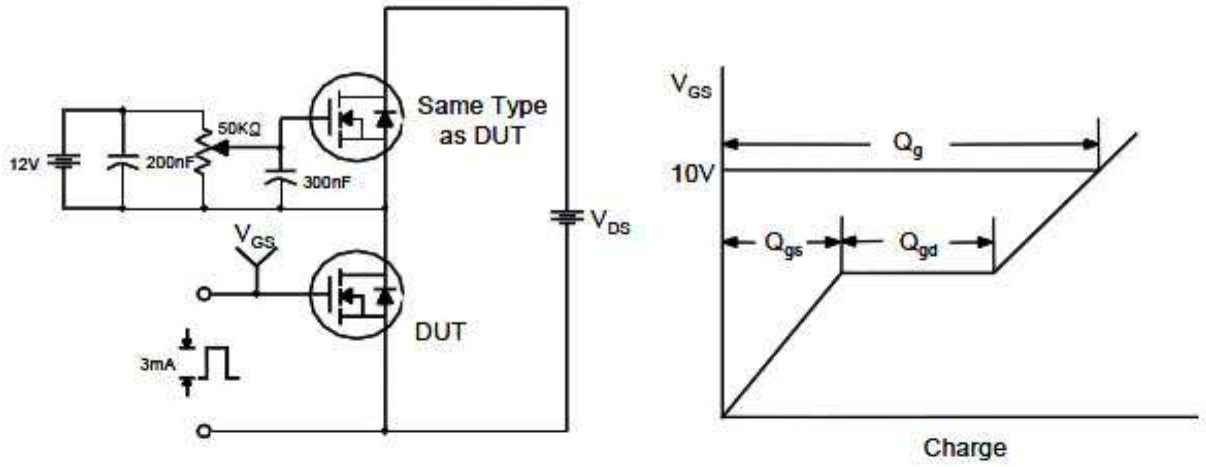


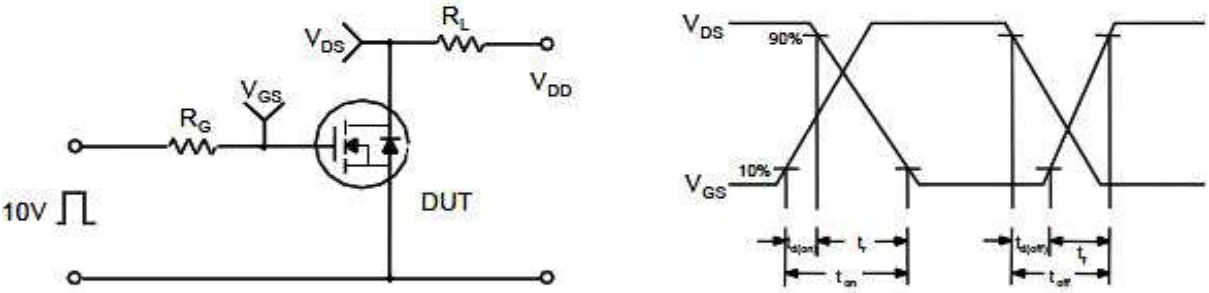
Fig.6 Maximum Safe Operation Area

Typical Performance Characteristics (Continue)

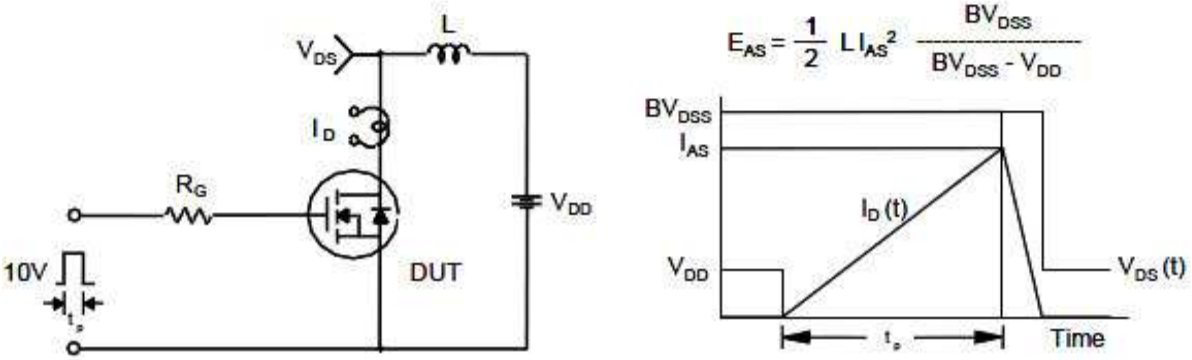
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

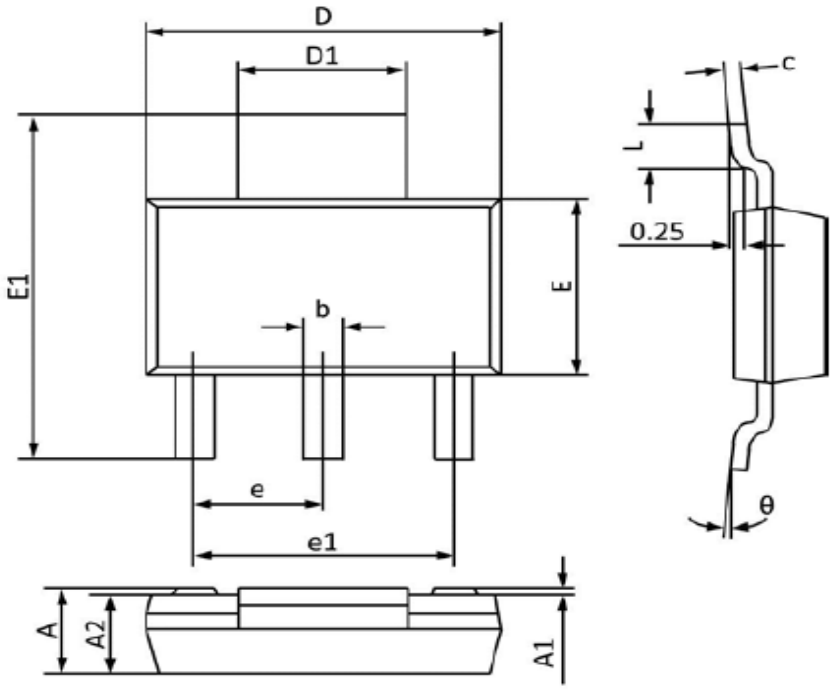


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

SOT-223



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.520	1.800	0.060	0.071
A1	0.000	0.100	0.000	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.820	0.026	0.032
c	0.250	0.350	0.010	0.014
D	6.200	6.400	0.244	0.252
D1	2.900	3.100	0.114	0.122
E	3.300	3.700	0.130	0.146
E1	6.830	7.070	0.269	0.278
e	2.300 (BSC)		0.091 (BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.150	0.035	0.045
θ	0°	10°	0°	10°

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